

BAW75 ~ BAW76

FEATURES :

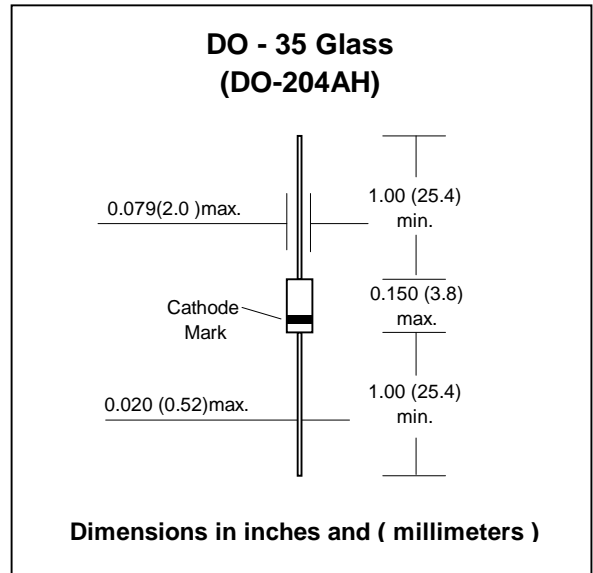
- High switching speed: max. 4 ns
- Reverse voltage: max. 25V , 50V
- Peak reverse voltage: max. 35V, 75 V
- Pb / RoHS Free

MECHANICAL DATA :

Case: DO-35 Glass Case

Weight: approx. 0.13g

HIGH SPEED SWITCHING DIODES



Maximum Ratings and Thermal Characteristics (Rating at 25 °C ambient temperature unless otherwise specified.)

Parameter		Symbol	Value	Unit
Maximum Peak Reverse Voltage	BAW75	V_{RM}	25	V
	BAW76		50	
Maximum Reverse Voltage	BAW75	V_{RM}	35	V
	BAW76		75	
Maximum Average Forward Current Half Wave Rectification with Resistive Load , $f \geq 50\text{Hz}$		$I_{F(AV)}$	150 ⁽¹⁾	mA
Maximum Power Dissipation		P_D	500 ⁽¹⁾	mW
Maximum Surge Forward Current at $t < 1\mu\text{s}$, $T_J = 25^\circ\text{C}$		I_{FSM}	2	A
Maximum Junction Temperature		T_J	200	°C
Storage Temperature Range		T_S	-65 to + 200	°C

Note : (1) Valid provided that leads are kept at ambient temperature at a distance of 8mm from case.

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Current	BAW75	I_R	$V_R = 25\text{V}$	-	-	100	nA
	BAW76		$V_R = 50\text{V}$	-	-	100	
Forward Voltage	BAW75	V_F	$I_F = 30\text{mA}$	-	-	1.0	V
	BAW76		$I_F = 100\text{mA}$	-	-	1.0	
Reverse Breakdown Voltage	BAW75	$V_{(BR)R}$	Test with $5\mu\text{A}$ pulses	35	-	-	V
	BAW76			75	-	-	
Diode Capacitance	BAW75	Cd	$f = 1\text{MHz}$; $V_R = 0$	-	-	4.0	pF
	BAW76			-	-	2.0	
Reverse Recovery Time		T_{rr}	$I_F = 10\text{mA}$, $I_R = 10\text{mA}$ $I_{rr} = 1\text{mA}$	-	-	4	ns

RATING AND CHARACTERISTIC CURVES (BAW75 ~ BAW76)

FIG. 1 ADMISSIBLE POWER DISSIPATION
VERSUS AMBIENT TEMPERATURE

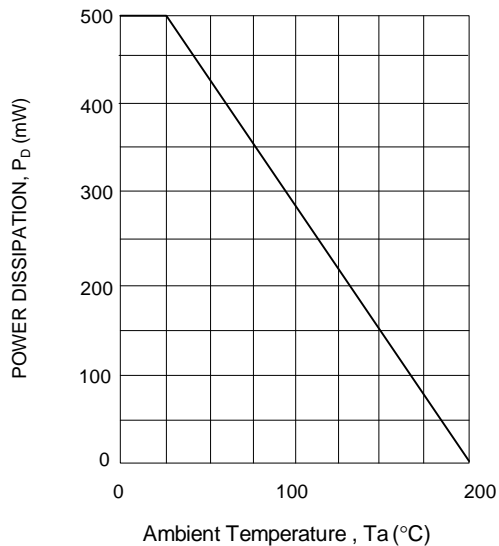


FIG. 2 TYPICAL FORWARD VOLTAGE

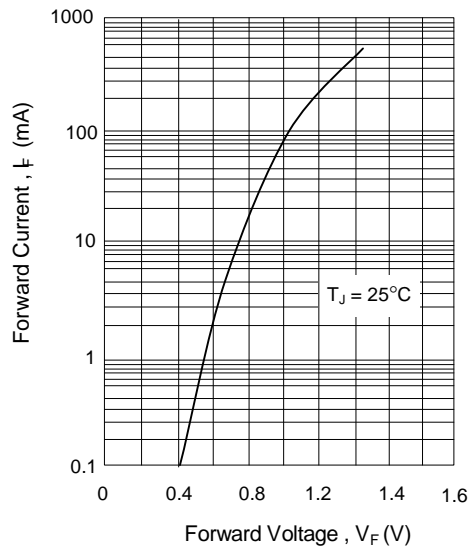


FIG. 3 TYPICAL DIODE CAPACITANCE AS
A FUNCTION OF REVERSE VOLTAGE

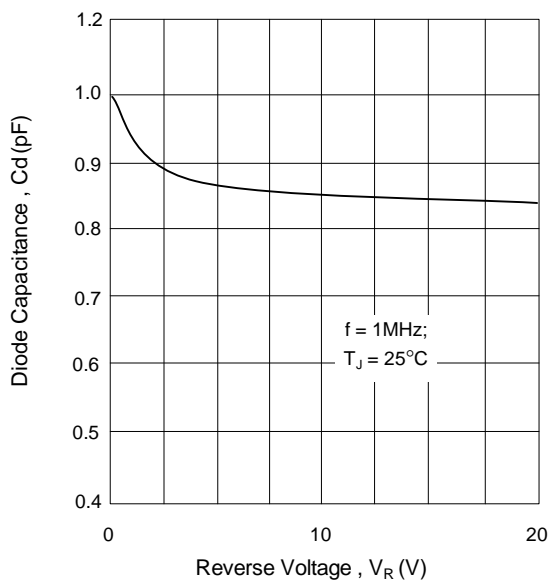


FIG. 4 TYPICAL REVERSE CURRENT
VERSUS JUNCTION TEMPERATURE

